

GT30J122

4TH GENERATION IGBT
CURRENT RESONANCE INVERTER SWITCHING APPLICATIONS

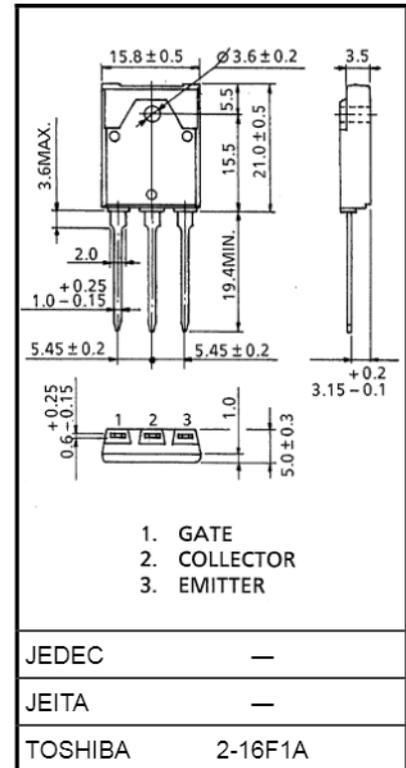
- Enhancement mode type
- High speed: $t_f = 0.25\mu s$ (Typ.) ($I_C = 50A$)
- Low saturation voltage: $V_{CE(sat)} = 2.1V$ (Typ.) ($I_C = 50A$)

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	600	V
Gate-emitter voltage	V_{GES}	± 20	V
Collector current	DC	I_C	30
	1 ms	I_{CP}	100
Collector power dissipation ($T_c = 25^\circ C$)	P_C	75	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



Weight: 5.8 g (typ.)